

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2SC2893** is Designed for use in UHF amplifiers up to 400 MHz.

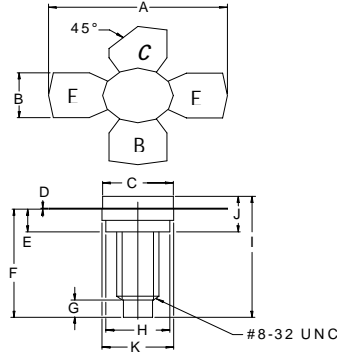
FEATURES:

- $P_{OUT} = 10.7$ W Typical at 400 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	1.5 A
V_{CB}	55 V
V_{CE}	32 V
V_{EB}	3.0 V
P_{DISS}	22 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	8.0 °C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 60$ mA	32			V
BV_{CES}	$I_C = 8.0$ mA $V_{BE} = 0$ V	55			V
I_{EBO}	$V_{CE} = 2.0$ V			500	μ A
I_{CBO}	$V_{CB} = 30$ V			500	μ A
h_{FE}	$V_{CE} = 10$ V $I_C = 400$ mA	20		200	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz		10	15	pF
P_{out}	$V_{CE} = 28$ V $I_C = 400$ mA $f = 400$ MHz	7.9	10.7		W
η_c	$P_{IN} = 0.63$ W	55	65		%